

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1084	349/43	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/04/2 5 11:43
2	BRS	L2	98	1 and (semiconductor with storage)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/04/2 5 14:49
3	BRS	L3	2	6493048.pn.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/04/2 5 11:50
4	BRS	L4	26	1 and (organic near inorganic)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/04/2 5 16:12

	Type	L #	Hits	Search Text	DBs	Time Stamp
5	BRS	L5	2	5233181.pn.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/04/2 5 14:56
6	BRS	L7	11	2 and doped near ((phosphorous antimony boron))	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/04/2 5 16:14
7	BRS	L6	51	1 and doped near ((phosphorous antimony boron))	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/04/2 5 16:19